

isc Silicon PNP Darlington Power Transistor

2SB1286

DESCRIPTION

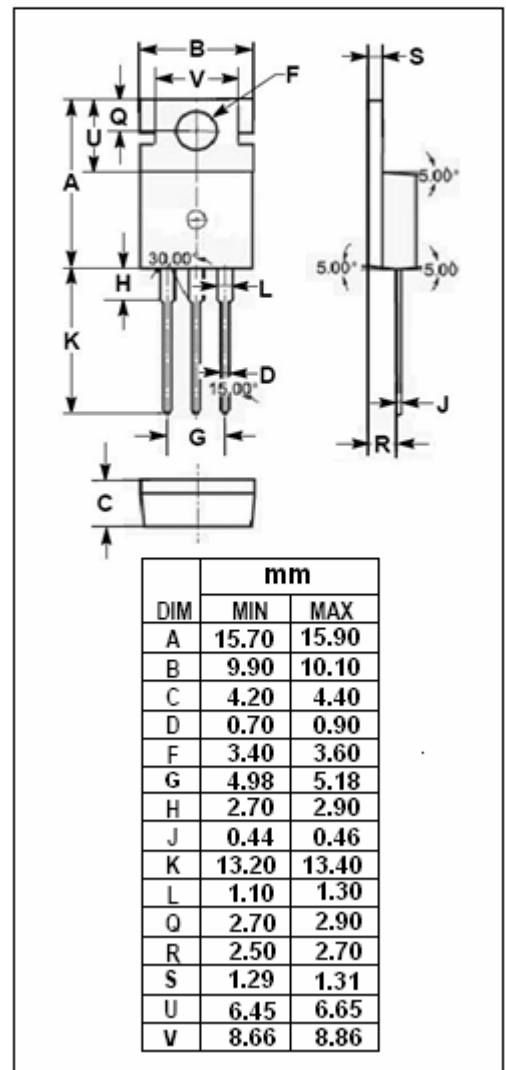
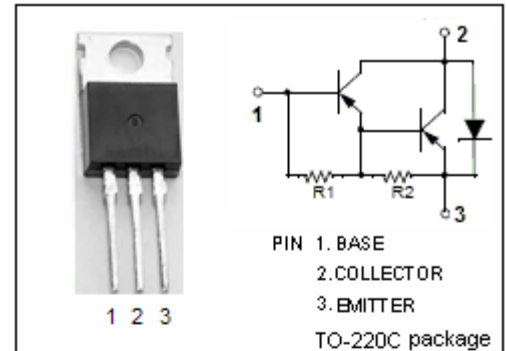
- High DC Current Gain-  
:  $h_{FE} = 1000(\text{Min}) @ I_C = -1\text{A}$
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = -100\text{V}(\text{Min})$
- Low Collector-Emitter Saturation Voltage  
:  $V_{CE(\text{sat})} = -1.5\text{V}(\text{Max}) @ I_C = -1\text{A}$
- Complement to Type 2SD1646

APPLICATIONS

- Designed for general purpose amplifier and low speed switching applications.

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	-100	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-100	V
V <sub>EBO</sub>	Emitter-Base Voltage	-8	V
I <sub>C</sub>	Collector Current-Continuous	-2	A
I <sub>CM</sub>	Collector Current-Peak	-3	A
P <sub>C</sub>	Collector Power Dissipation T <sub>C</sub> =25°C	25	W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C



**isc Silicon PNP Darlington Power Transistor****2SB1286****ELECTRICAL CHARACTERISTICS** **$T_C=25^{\circ}\text{C}$  unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -5\text{mA}$ , $I_B = 0$	-100			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -50\ \mu\text{A}$ , $I_E = 0$	-100			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -1\text{A}$ ; $I_B = -1\text{mA}$			-1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -100\text{V}$ ; $I_E = 0$			-10	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -7\text{V}$ ; $I_C = 0$			-3	mA
$h_{FE}$	DC Current Gain	$I_C = -1\text{A}$ ; $V_{CE} = -2\text{V}$	1000		10000	
$C_{OB}$	Output Capacitance	$I_E = 0$ ; $V_{CB} = -10\text{V}$ ; $f = 1\text{MHz}$		35		pF